

### ABSTRACT

5 The present invention relates to a surface protecting adhesive film for a semiconductor wafer in which an adhesive layer having a storage elastic modulus from  $1 \times 10^5$  Pa to  $1 \times 10^7$  Pa at 150 °C and a thickness of from 3  $\mu\text{m}$  to 100  $\mu\text{m}$  is formed on both a surface and back surface of a base film having a melting point of at least 200°C and a thickness of 10  $\mu\text{m}$  to 200  $\mu\text{m}$ . According to the present invention, in a step of grinding the back side of a semiconductor wafer and removing a damaged layer generated on the back side, the semiconductor wafer can be prevented from being broken and being contaminated and the like even if a semiconductor wafer is thinned as low as 100  $\mu\text{m}$ .